

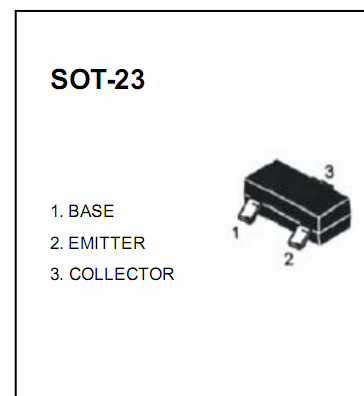
TRANSISTOR (PNP)

FEATURES

Complimentary to SS8050

MARKING: Y2

**MAXIMUM RATINGS** (TA=25°C unless otherwise noted)



| Symbol<br>(符号) | Parameter<br>(参数名称)                   | Value<br>(额定值) | Units<br>(单位) |
|----------------|---------------------------------------|----------------|---------------|
| VCBO           | Collector-Base Voltage (集电极-基极电压)     | -40            | V             |
| VCEO           | Collector-Emitter Voltage (集电极-发射极电压) | -25            | V             |
| VEBO           | Emitter-Base Voltage (发射极-基极电压)       | -5             | V             |
| IC             | Collector Current -Continuous (集电极电流) | -1.5           | A             |
| PC             | Collector Power Dissipation (耗散功率)    | 0.3            | W             |
| Tj             | Junction Temperature (结温)             | 150            | °C            |
| Tstg           | Storage Temperature (储存温度)            | -55-150        | °C            |

**ELECTRICAL CHARACTERISTICS** (Tamb=25°C unless otherwise specified)

| Parameter<br>(参数名称)                                 | Symbol<br>(符号) | Test conditions<br>(测试条件) | MIN<br>(最小值) | TYP<br>(典型值) | MAX<br>(最大值) | UNIT<br>(单位) |
|-----------------------------------------------------|----------------|---------------------------|--------------|--------------|--------------|--------------|
| Collector-base breakdown voltage<br>集电极-基极击穿电压      | V(BR)CBO       | IC= -100μA, IE=0          | -40          |              |              | V            |
| Collector-emitter breakdown voltage<br>集电极-发射极击穿电压  | V(BR)CEO       | IC= -1mA, IB=0            | -25          |              |              | V            |
| Emitter-base breakdown voltage<br>发射极-基极击穿电压        | V(BR)EBO       | IE=-100μA, IC=0           | -5           |              |              | V            |
| Collector cut-off current<br>集电极-基极截止电流             | ICBO           | VCB=-25 V, IE=0           |              |              | -1           | μ A          |
| Collector cut-off current<br>集电极-发射极截止电流            | ICEO           | VCE=-15V, IB=0            |              |              | -10          | μ A          |
| Emitter cut-off current<br>发射极-基极截止电流               | IEBO           | VEB=-5V, IC=0             |              |              | -1           | μ A          |
| DC current gain<br>直流电流增益                           | hFE            | VCE=-1V, IC= -100mA       | 80           |              | 400          |              |
| Collector-emitter saturation voltage<br>集电极-发射极饱和压降 | VCE(sat)       | IC=-800mA, IB= -80mA      |              |              | -0.5         | V            |
| Base-emitter saturation voltage<br>发射极-基极饱和压降       | VBE(sat)       | IC=-800mA, IB= -80mA      |              |              | -1.2         | V            |

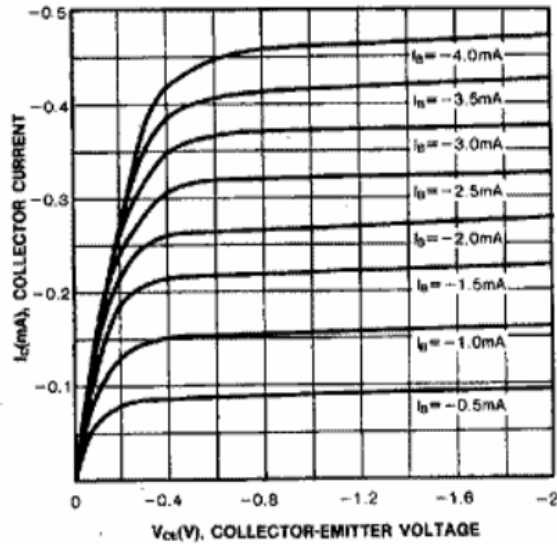
**CLASSIFICATION OF hFE**

| Range | 80-100 | 100-200 | 200-400 |
|-------|--------|---------|---------|
|-------|--------|---------|---------|

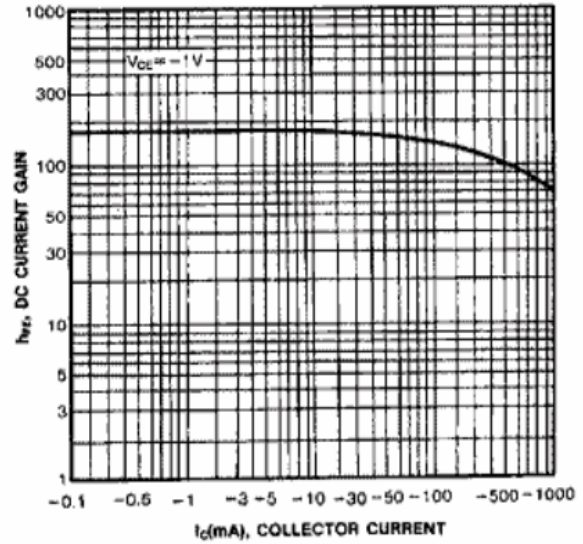


## Typical Characteristics

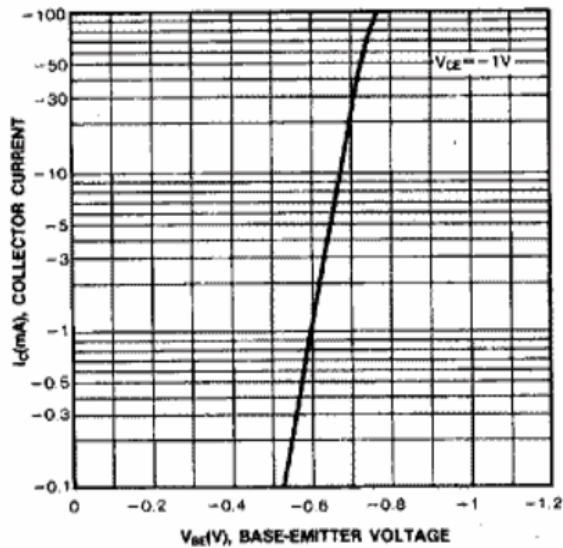
STATIC CHARACTERISTIC



DC CURRENT GAIN



BASE-EMITTER ON VOLTAGE



BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE

